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PATENT

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TELEPHONE MAIL ROOM

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Willis, Stephen L.) Group Art Unit 2815
Appl. No. : 09/552,383)
Filed : 04/19/2000)
For : CHEMICAL MECHANICAL)
PLANARIZATION OF)
CONDUCTIVE MATERIAL)
Examiner : Diaz, Jose R.)

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action mailed March 14, 2002 (Paper No. 9), please amend the above-captioned application as follows.

IN THE CLAIMS:

Please add new claims as follows:

56. (New) A method of forming a dielectric layer of a first thickness on a semiconductor wafer, the method comprising:
forming the dielectric layer of the first thickness on the wafer;
positioning a shield layer on the dielectric layer;
positioning a sacrificial layer on the shield layer;
depositing conductive material on the sacrificial layer;